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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Wu et al.

Attorney Docket No.: NOVLP094

Application No.: 10/789,103

Examiner: Not Yet Assigned

Filed: February 27, 2004

Group: 1762

Title: METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS

Confirmation No.: 7687

**CERTIFICATE OF MAILING** 

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail on June 23, 2005 in an envelope addressed to: Mall Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signed:

Tara Hayden

INFORMATION DISCLOSURE STATEMENT 37 CFR §§1.56 AND 1.97(b)

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

The references listed in the attached PTO Form 1449, copies of which are attached, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

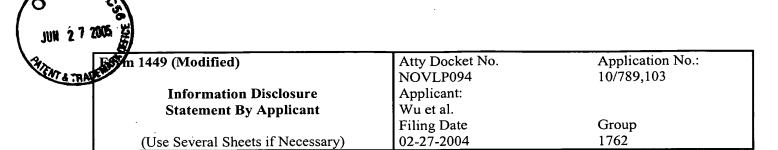
This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. NOVLP094).

Respectfully submitted,

BEYER WEAVER & THOMAS, LLP

P.O. Box 70250 Oakland, CA 94612-0250 Jeffrey K. Weaver Registration No. 31,314



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